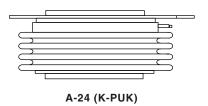


Phase Control Thyristors (Hockey PUK Version), 1473 A



PRODUCT SUMMARY	
I _{T(AV)}	1473 A

FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-24 (K-PUK)
- High profile hockey PUK
- Compliant to RoHS Directive 2002/95/EC



TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		1473	А			
I _{T(AV)}	T _{hs}	55	°C			
L		2913	А			
I _T (RMS)	T _{hs}	25	°C			
1	50 Hz	20.0	A			
I _{TSM}	60 Hz	21.2	A			
124	50 Hz	2000	kA ² s			
l ² t	60 Hz	1865	KA-S			
l²√t		20 000	kA ² √s			
V _{DRM} /V _{RRM}	Range	1200 to 2600	V			
t _q	Typical	300	μs			
TJ	Range	- 40 to 125	°C			

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	REVERSE VOI TAGE		I _{RRM} MAXIMUM AT T _J = 125 °C mA				
	12	1200	1300					
	16	1600	1700					
	18	1800	1900					
ST1000CK	20	2000	2100	100				
	22	2200	2300					
	24	2400	2500					
	26	2600	2700					

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ST1000C..K Series

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ABSOLUTE MAXIMUM RATINGS	5					
PARAMETER	SYMBOL		VALUES	UNITS		
Maximum average on-state current	1	180° condu	180° conduction, half sine wave			Α
at heatsink temperature	I _{T(AV)}	Double side	(single side) co	oled	55 (85)	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink tempe	erature double side cooled	6540	Α
		t = 10 ms	No voltage		20.0	
Maximum peak, one-cycle,	L	t = 8.3 ms	reapplied		21.2	kA kA ² s
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		17.0	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	18.1	
Maximum I ² t for fusing	l ² t	t = 10 ms	No voltage reapplied	initial T _J = T _J maximum	2000	
		t = 8.3 ms			1865	
		t = 10 ms			1445	
		t = 8.3 ms	reapplied		1360	
Maximum I ² √t for fusing	I ² √t	t = 0.1 ms to	t = 0.1 ms to 10 ms, no voltage reapplied			kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.950	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			V
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			mΩ
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.265	11152
Maximum on-state voltage drop	V_{TM}	$I_{pk} = 3000 \text{ A}, T_J = 125 ^{\circ}\text{C}, t_p = 10 \text{ ms sine pulse}$			1.80	V
Maximum holding current	I _H	T _ 05 °C	anada aunnhi 1	2 V registive lead	600	mA
Typical latching current	ΙL	T _J = 25 °C, anode supply 12 V resistive load			1000	IIIA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/μs
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1$ A/ μ s $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.9	
Typical turn-off time	t _q	$I_{TM} = 550 \text{ A, } T_J = T_J \text{ maximum, dI/dt} = 40 \text{ A/}\mu\text{s,}$ $V_R = 50 \text{ V, dV/dt} = 20 \text{ V/}\mu\text{s, gate 0 V 100 }\Omega, t_p = 500 \mu\text{s}$	300	μs

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 80 % rated V _{DRM}	500	V/µs	
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	100	mA	



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TRIGGERING						
DADAMETED	CVMDOL			VALUES		
PARAMETER	SYMBOL	16	ST CONDITIONS	TYP.	MAX.	UNITS
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	, t _p ≤ 5 ms	16		w
Maximum peak average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	, f = 50 Hz, d% = 50	(3] vv
Maximum peak positive gate current	I _{GM}			3	.0	Α
Maximum peak positive gate voltage	+ V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms		2	.0	V
Maximum peak negative gate voltage	- V _{GM}			5.0		7
		T _J = - 40 °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units	200	-	
DC gate current required to trigger	I _{GT}	T _J = 25 °C		100	200	mA
		T _J = 125 °C		50	-	
		T _J = - 40 °C		1.4	-	
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C	12 V anode to cathode applied	1.1	3.0	V
		T _J = 125 °C		0.9	-	
DC gate current not to trigger	I _{GD}	T T	Maximum gate current/voltage not to trigger is the maximum	10		mA
DC gate voltage not to trigger	V _{GD}	$T_J = T_J$ maximum	value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.:	25	V

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating temperature range	TJ		- 40 to 125	- °C		
Maximum storage temperature range	T _{Stg}		- 40 to 150			
Maximum thermal resistance,	D	DC operation single side cooled	0.042			
junction to heatsink	R _{thJ-hs}	DC operation double side cooled	0.021	K/W		
Maximum thermal resistance,	В	DC operation single side cooled	0.006	IV VV		
case to heatsink	R _{thC-hs}	DC operation double side cooled	0.003			
Mounting force, ± 10 %			24 500	N		
Widdining force, ± 10 %			(2500)	(kg)		
Approximate weight			425	g		
Case style		See dimensions - link at the end of datasheet	A-24 (K-P	UK)		

△R _{thJC} CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL	CONDUCTION	RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS
180°	0.003	0.003	0.002	0.002		
120°	0.004	0.004	0.004	0.004	$T_J = T_J$ maximum	
90°	0.005	0.005	0.005	0.005		K/W
60°	0.007	0.007	0.007	0.007		
30°	0.012	0.012	0.012	0.012		

Note

 $\bullet \quad \text{The table above shows the increment of thermal resistance } R_{\text{thJC}} \text{ when devices operate at different conduction angles than DC} \\$

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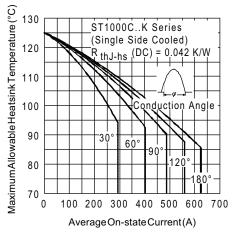


Fig. 1 - Current Ratings Characteristics

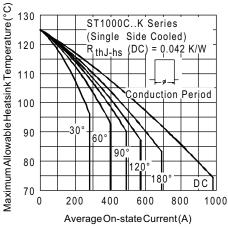


Fig. 2 - Current Ratings Characteristics

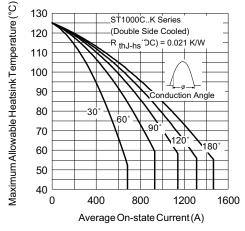


Fig. 3 - Current Ratings Characteristics

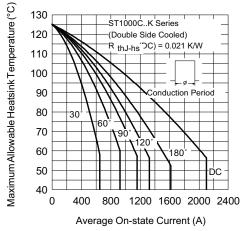


Fig. 4 - Current Ratings Characteristics

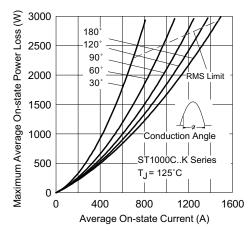


Fig. 5 - On-State Power Loss Characteristics

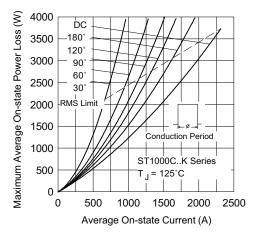
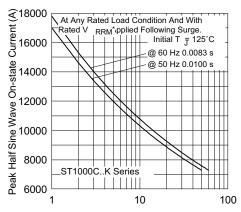


Fig. 6 - On-State Power Loss Characteristics



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Number Of Equal Amplitude Half Cycle Current Pulses (N)

Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

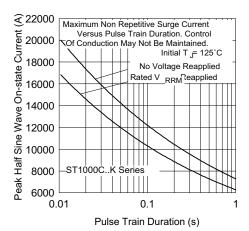


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

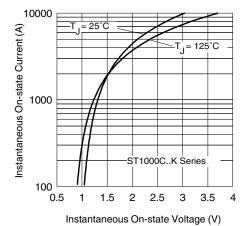


Fig. 9 - On-State Voltage Drop Characteristics

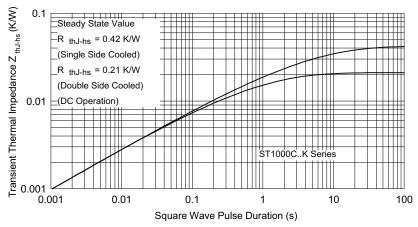


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

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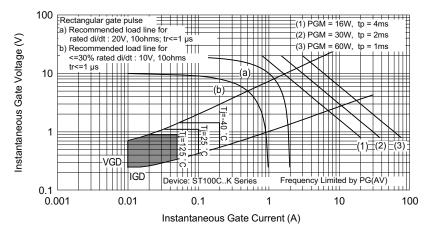
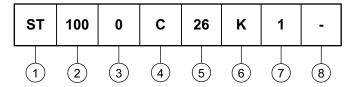


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



1 - Thyristor

2 - Essential part number

3 - 0 = Converter grade

4 - C = Ceramic PUK

5 - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)

6 - K = PUK case A-24 (K-PUK)

7 - 0 = Eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = Fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = Eyelet terminals (gate and auxiliary cathode soldered leads)

3 = Fast-on terminals (gate and auxiliary cathode soldered leads)

8 - Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

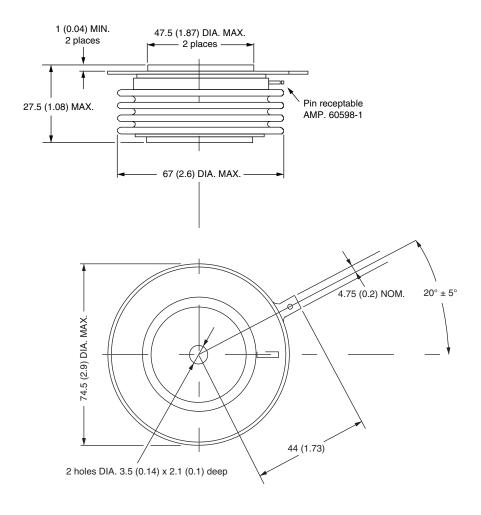
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95081			

For technical questions, contact: indmodules@vishay.com

A-24 (K-PUK)

DIMENSIONS in millimeters (inches)

Creepage distance: 28.88 (1.137) minimum Strike distance: 17.99 (0.708) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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